

PDT2955S

60V P-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	110mΩ@-10V	-2.5A
	135mΩ@-4.5V	

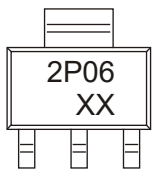
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

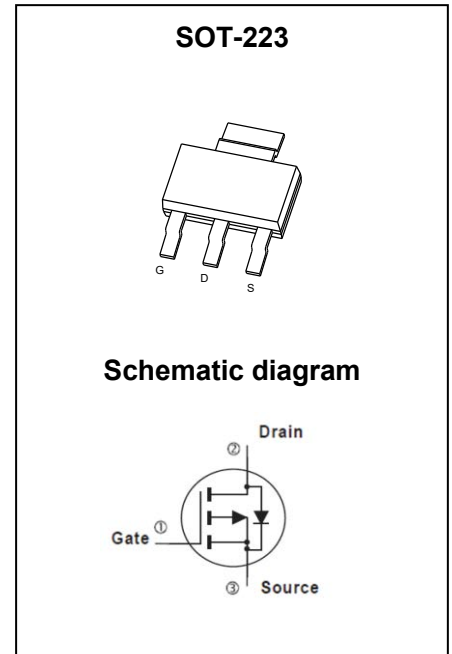
Application

- DC/DC Converter
- Power Management

MARKING:



2P06 = Device Code
XX = Date Code



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	-60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^{1,5}	I_D	-2.5	A
Pulsed Drain Current ²	I_{DM}	-8.5	A
Power Dissipation ⁵	P_D	1.7	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	75	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

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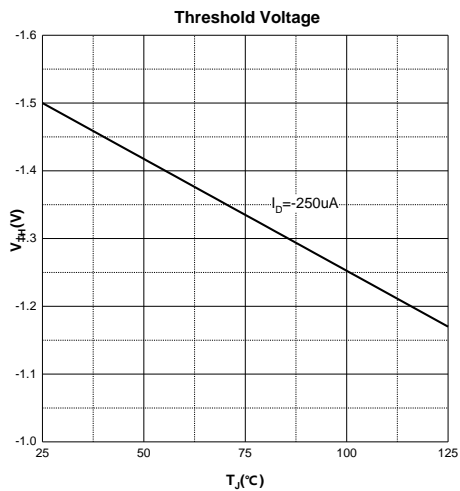
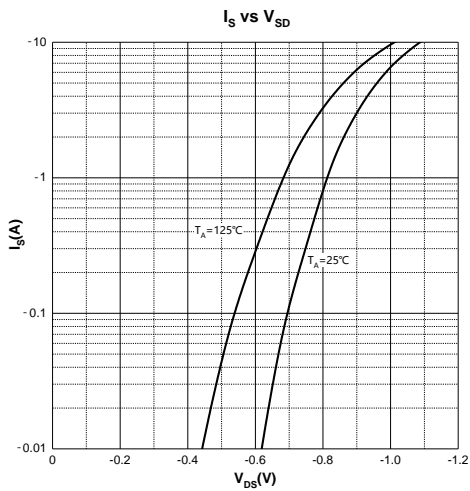
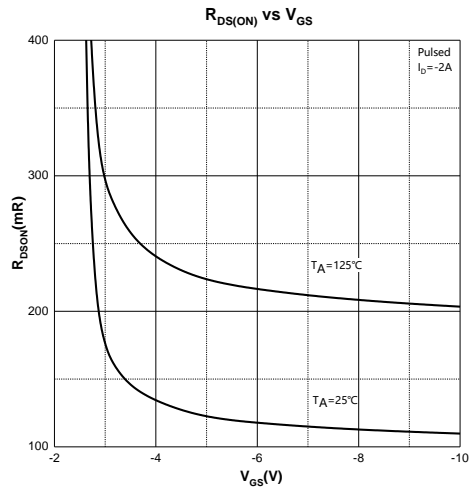
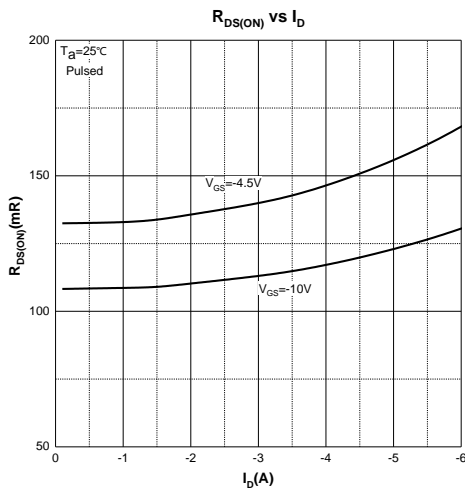
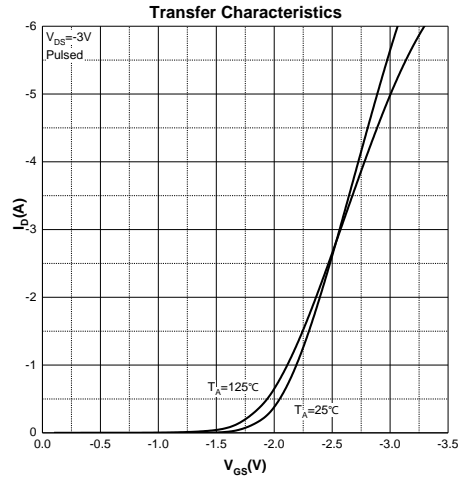
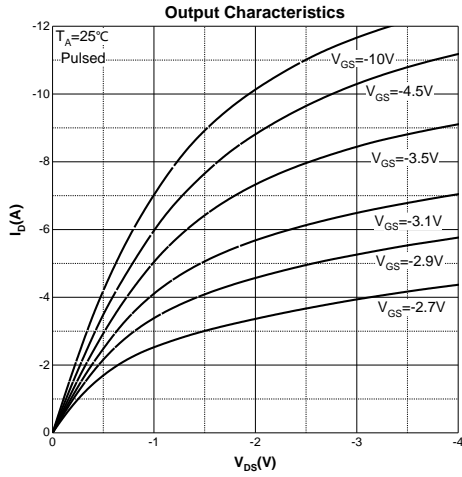
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -48V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -2.0A$		110	190	m Ω
		$V_{GS} = -4.5V, I_D = -1.0A$		135	240	
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -2.0A$	2			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V, f = 1MHz$		350		pF
Output Capacitance	C_{oss}			32		
Reverse Transfer Capacitance	C_{rss}			26		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -30V, V_{GS} = -10V, I_D = -2.0A$		7		nC
Gate-source Charge	Q_{gs}			2.2		
Gate-drain Charge	Q_{gd}			3		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -10V,$ $R_L = 15\Omega, R_G = 3\Omega$		7		ns
Turn-on Rise Time	t_r			6		
Turn-off Delay Time	$t_{d(off)}$			12		
Turn-off Fall Time	t_f			7		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -2.0A$			-1.2	V

Notes :

- 1.The maximum current rating is limited by Chip.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



PDT2955S

SOT-223 Package Information

尺寸 标注	最小 (mm)	最大 (mm)	尺寸 标注	最小 (mm)	最大 (mm)
A	6.40	6.60	C	1.45	1.65
e	2.286 (BSC)		C1	0.03	0.15
b	0.66	0.76	C2	0.20	0.35
b1	2.95	3.05	L	0.76	1.16
B	3.40	3.60	L1	1.70	1.80
B1	6.85	7.15	θ	0°	8°

